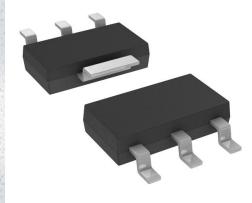


SPZT3904T1G Datasheet

www.digi-electronics.com



DiGi Electronics Part Number	SPZT3904T1G-DG
Manufacturer	onsemi
Manufacturer Product Number	SPZT3904T1G
Description	TRANS NPN 40V 0.2A SOT223
Detailed Description	Bipolar (BJT) Transistor NPN 40 V 200 mA 300MHz 1 .5 W Surface Mount SOT-223 (TO-261)

https://www.DiGi-Electronics.com



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Purchase and inquiry

anufacturer Product Number:	Manufacturer:
PZT3904T1G	onsemi
eries:	Product Status:
	Active
ansistor Type:	Current - Collector (Ic) (Max):
PN	200 mA
oltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
٧	300mV @ 5mA, 50mA
urrent - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
	100 @ 10mA, 1V
ower - Max:	Frequency - Transition:
5 W	300MHz
perating Temperature:	Grade:
55°C ~ 150°C (TJ)	Automotive
ualification:	Mounting Type:
EC-Q101	Surface Mount
ackage / Case:	Supplier Device Package:
D-261-4, TO-261AA	SOT-223 (TO-261)
ase Product Number:	
PZT3904	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0075	

onsemi

General Purpose Transistor

NPN Silicon

PZT3904T1G

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

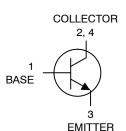
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector – Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	200	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

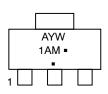
Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) T _A = 25°C	P _D	1.5 12	W mW/°C
Thermal Resistance Junction-to-Ambient (Note 1)	R_{\thetaJA}	83.3	°C/W
Thermal Resistance Junction-to-Lead #4	$R_{\theta JA}$	35	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

1. FR-4 with 1 oz and 713 mm² of copper area.





MARKING DIAGRAM



1AM = Specific Device Code

= Assembly Location

Y = Year

А

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
PZT3904T1G	SOT–223 (Pb–Free)	1,000 / Tape & Reel
SPZT3904T1G	SOT–223 (Pb–Free)	1,000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SPZT3904T1G onsemi TRANS NPN 40V 0.2A SOT223

PZT3904T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (Note 2)				
Collector – Emitter Breakdown Voltage (Note 3) ($I_c = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	40	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \ \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	60	-	
Emitter – Base Breakdown Voltage (I _E = 10 μ Adc, I _C = 0)	V _{(BR)EBO}	6.0	-	
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	-	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	_	50	

ON CHARACTERISTICS (Note 3)

$ \begin{array}{l} \text{DC Current Gain (Note 2)} \\ (I_{C} = 0.1 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 50 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc, } V_{CE} = 1.0 \text{ Vdc}) \end{array} $	H _{FE}	40 70 100 60 30	- - 300 - -	-
Collector – Emitter Saturation Voltage (Note 3) ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}		0.2 0.3	Vdc
Base – Emitter Saturation Voltage (Note 3) ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C _{obo}	-	5.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	8.0	
Input Impedance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{ie}	1.0	10	kΩ
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{re}	0.5	8.0	X 10 ⁻⁴
Small-Signal Current Gain (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{fe}	100	400	-
Output Admittance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{oe}	1.0	40	μMhos
Noise Figure (V _{CE} = 5.0 Vdc, I _C = 100 μ Adc, R _S = 1.0 kΩ, f = 1.0 kHz)	nF	-	5.0	dB

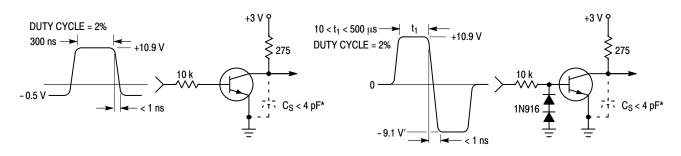
SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = – 0.5 Vdc,	t _d	-	35	ns
Rise Time	$I_{\rm C}$ = 10 mAdc, $I_{\rm B1}$ = 1.0 mAdc)	t _r	-	35	
Storage Time	(V _{CC} = 3.0 Vdc,	t _s	-	200	
Fall Time	$I_{\rm C}$ = 10 mAdc, $I_{\rm B1}$ = $I_{\rm B2}$ = 1.0 mAdc)	t _f	-	50	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

 $\begin{array}{ll} \text{2. } FR-5 = 1.0 \times 0.75 \times 0.062 \text{ in.} \\ \text{3. } Pulse \mbox{ Test: Pulse Width } \leq 300 \ \mu \text{s, Duty Cycle} \leq 2.0\%. \end{array}$

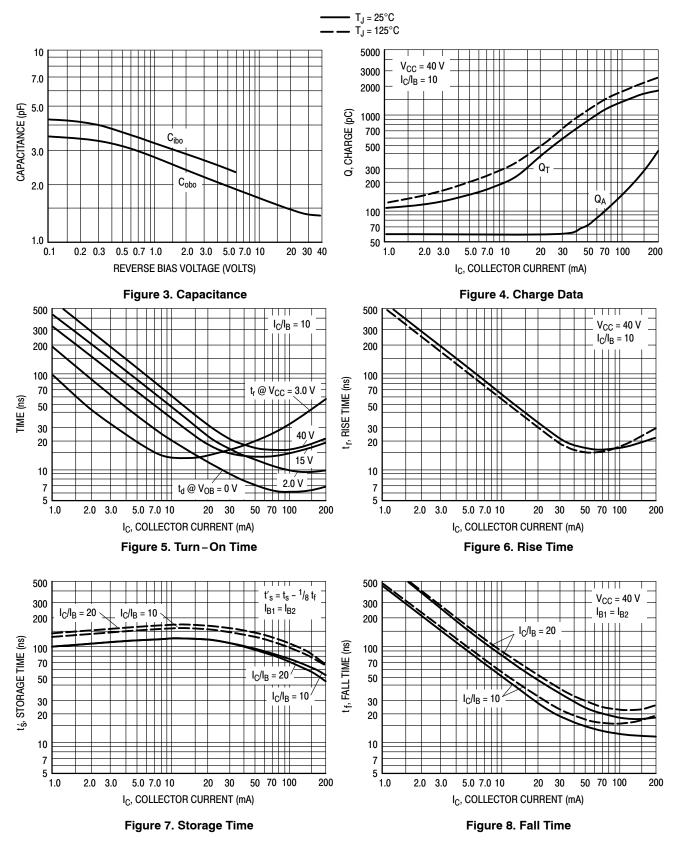




* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ VDC}, T_A = 25^{\circ}\text{C}, BANDWIDTH = 1.0 \text{ HZ})$

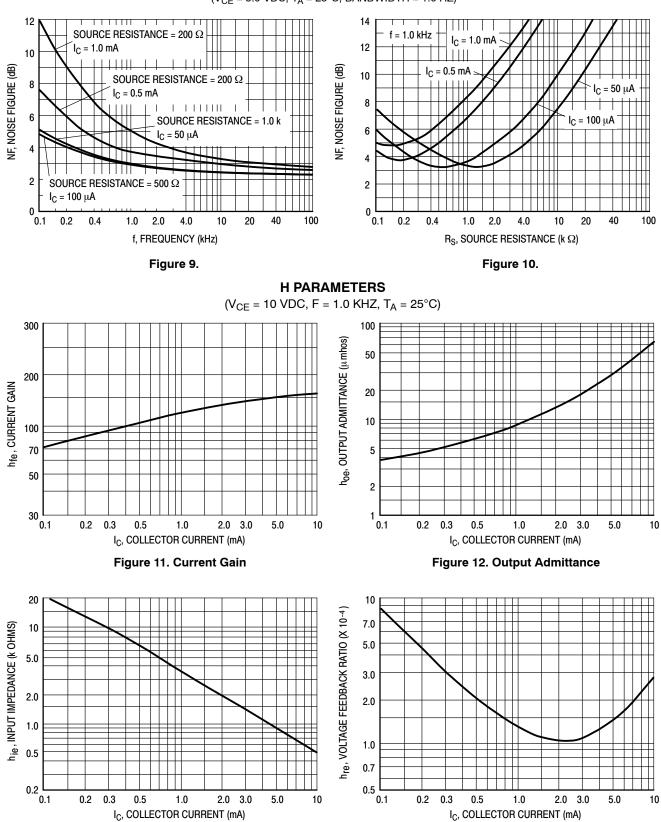
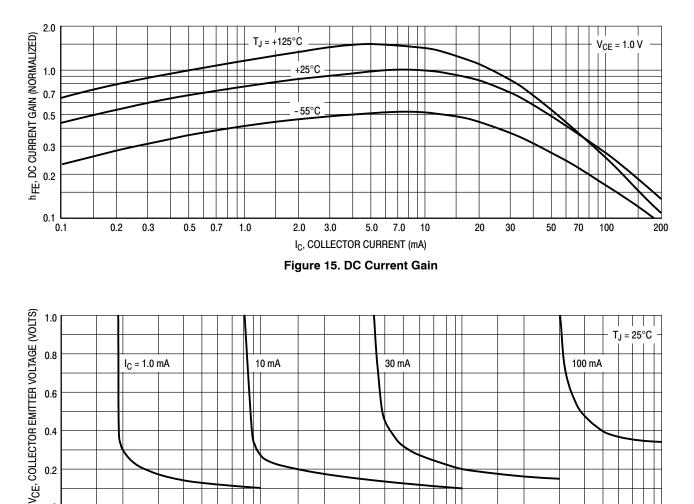


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS



0.6

0.4

0.2

0

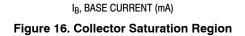
0.01

0.02

0.03

0.05

0.07 0.1



0.3

0.2

0.5

0.7

1.0

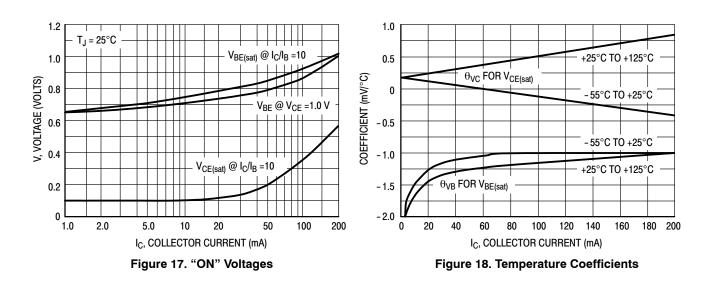
2.0

3.0

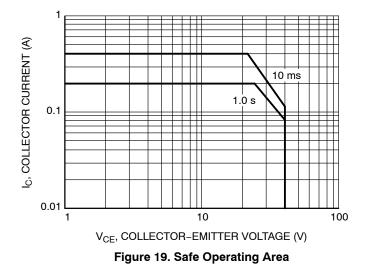
5.0

7.0

10



TYPICAL CHARACTERISTICS



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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

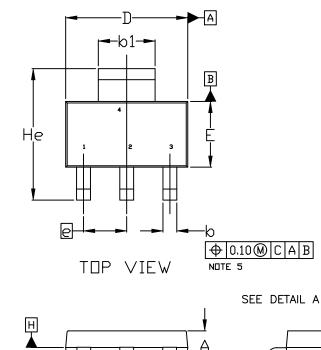
SCALE 1:1

0.10 C

A1

SOT-223 (TO-261) CASE 318E-04 ISSUE R

DATE 02 OCT 2018



SIDE VIEW

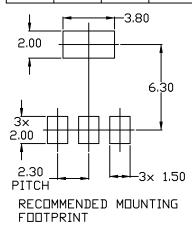
DETAIL A

1

FRONT VIEW

- NDTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- AI IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS		
DIM	MIN.	NDM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
с	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20		
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0*		10*



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DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: Pin 1. Source 2. Drain 3. Gate 4. Drain	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
Style 6: Pin 1. Return 2. Input 3. Output 4. Input	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	Style 9: Pin 1. Input 2. Ground 3. Logic 4. Ground	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package
- (Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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